

Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness
- Halogen Free, RoHS Compliant

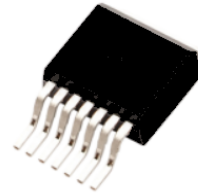
Benefits

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

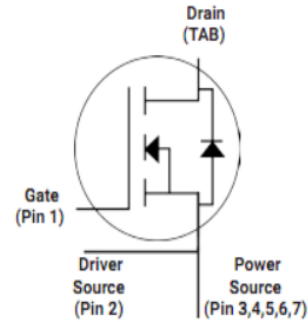
Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power applications

Package



TO-263-7L



Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	
V_{GSmax}	Gate - Source Voltage	-10/+25	V	Absolute maximum values	
V_{GSop}	Gate - Source Voltage	-5/+20	V	Recommended operational values	
I_D	Continuous Drain Current	31	A	$V_{GS} = 20\text{ V}, T_c = 25^\circ\text{C}$	Fig. 19
		24		$V_{GS} = 20\text{ V}, T_c = 100^\circ\text{C}$	
$I_{D(pulse)}$	Pulsed Drain Current	80	A	Pulse width t_p limited by T_{jmax}	Fig. 22
P_D	Power Dissipation	200	W	$T_c = 25^\circ\text{C}, T_j = 150^\circ\text{C}$	Fig. 20
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		
T_L	Solder Temperature	260	$^\circ\text{C}$	1.6mm (0.063") from case for 10s	
M_d	Mounting Torque	1 8.8	Nm lbf-in	M3 or 6-32 screw	

Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.5	4	V	$V_{DS} = V_{GS}, I_D = 5\text{ mA}$	Fig. 11
			1.8		V	$V_{DS} = V_{GS}, I_D = 5\text{ mA}, T_J = 150^\circ\text{C}$	
I_{DSS}	Zero Gate Voltage Drain Current		1	100	μA	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	
I_{GSS}	Gate-Source Leakage Current			250	nA	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	
$R_{DS(on)}$	Drain-Source On-State Resistance		80	98	m Ω	$V_{GS} = 20\text{ V}, I_D = 20\text{ A}$	Fig. 4, 5, 6
			120			$V_{GS} = 20\text{ V}, I_D = 20\text{ A}, T_J = 150^\circ\text{C}$	
g_{fs}	Transconductance		7.0		S	$V_{DS} = 20\text{ V}, I_{DS} = 20\text{ A}$	Fig. 7
			6.6			$V_{DS} = 20\text{ V}, I_{DS} = 20\text{ A}, T_J = 150^\circ\text{C}$	
C_{iss}	Input Capacitance		1980		pF	$V_{GS} = 0\text{ V}$ $V_{DS} = 1000\text{ V}$ $f = 1\text{ MHz}$	Fig. 17, 18
C_{oss}	Output Capacitance		91				
C_{rss}	Reverse Transfer Capacitance		1.8				
E_{oss}	C_{oss} Stored Energy		45		μJ	$V_{AC} = 25\text{ mV}$	Fig. 16
E_{AS}	Avalanche Energy, Single Pluse		0.8		J	$I_D = 20\text{ A}, V_{DD} = 50\text{ V}$	Fig. 29
E_{ON}	Turn-On Switching Energy		400		μJ	$V_{DS} = 800\text{ V}, V_{GS} = -5/20\text{ V}, I_D = 20\text{ A},$ $R_{G(ext)} = 2.5\text{ }\Omega, L = 142\text{ }\mu\text{H}$	Fig. 25
E_{OFF}	Turn Off Switching Energy		150				
$t_{d(on)}$	Turn-On Delay Time		44		ns	$V_{DD} = 800\text{ V}, V_{GS} = -5/20\text{ V}$ $I_D = 20\text{ A}, R_{G(ext)} = 2.5\text{ }\Omega,$ $R_L = 40\text{ }\Omega$, Timing relative to V_{DS} Per IEC60747-8-4 pg 83	Fig. 27
t_r	Rise Time		76				
$t_{d(off)}$	Turn-Off Delay Time		42				
t_f	Fall Time		21				
$R_{G(int)}$	Internal Gate Resistance		2.0		Ω	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$	
Q_{gs}	Gate to Source Charge		18		nC	$V_{DS} = 800\text{ V}, V_{GS} = -5/20\text{ V}$ $I_D = 20\text{ A}$ Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		23				
Q_g	Total Gate Charge		102				

Reverse Diode Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	3.5		V	$V_{GS} = -5\text{ V}, I_{SD} = 10\text{ A}$	Fig. 8, 9, 10
		3.3		V	$V_{GS} = -5\text{ V}, I_{SD} = 10\text{ A}, T_J = 150^\circ\text{C}$	
I_S	Continuous Diode Forward Current		31	A	$T_c = 25^\circ\text{C}$	Note 1
t_{rr}	Reverse Recover time	32		ns	$V_{GS} = -5\text{ V}, I_{SD} = 20\text{ A}, V_R = 800\text{ V}$ $\text{dif}/\text{dt} = 2400\text{ A}/\mu\text{s}$	Note 1
Q_{rr}	Reverse Recovery Charge	192		nC		
I_{rrm}	Peak Reverse Recovery Current	10		A		

Note (1): When using SiC Body Diode the maximum recommended $V_{GS} = -5\text{ V}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.60	0.65	$^\circ\text{C}/\text{W}$		Fig. 21
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient		40			

Typical Performance

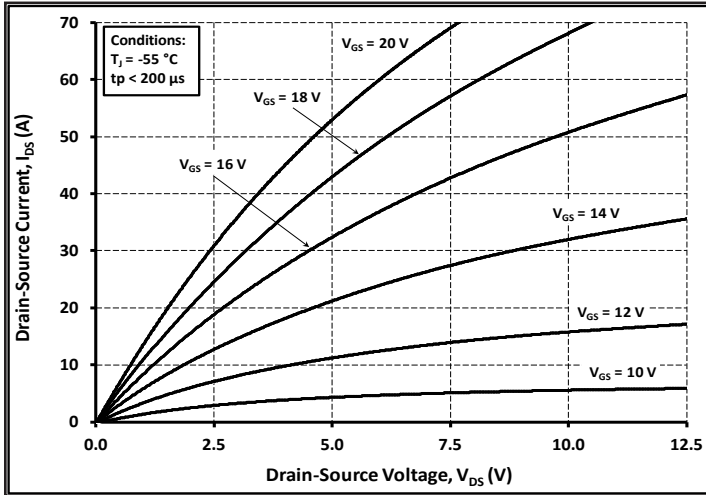
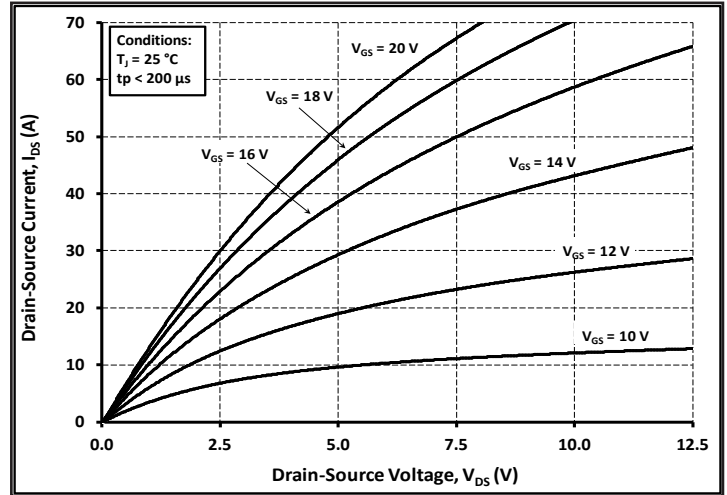
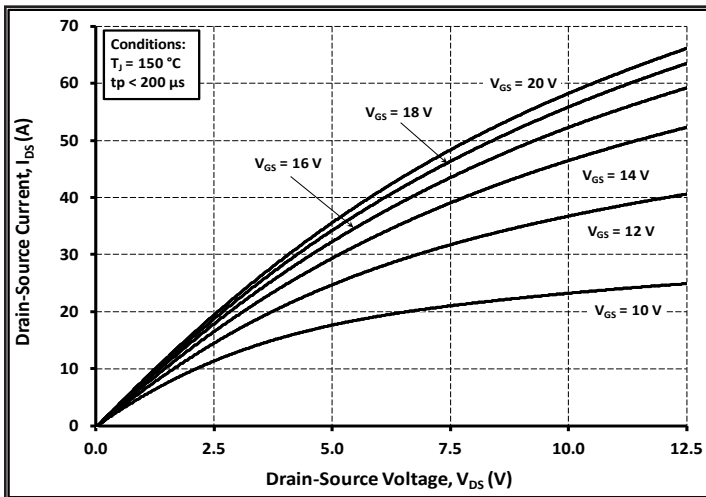
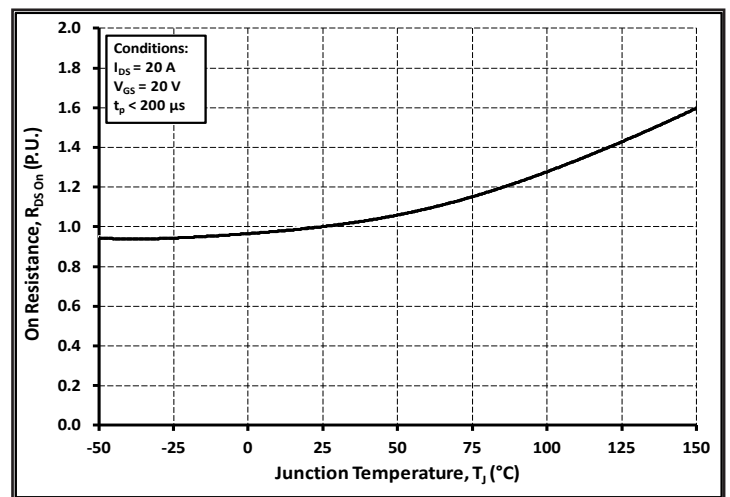
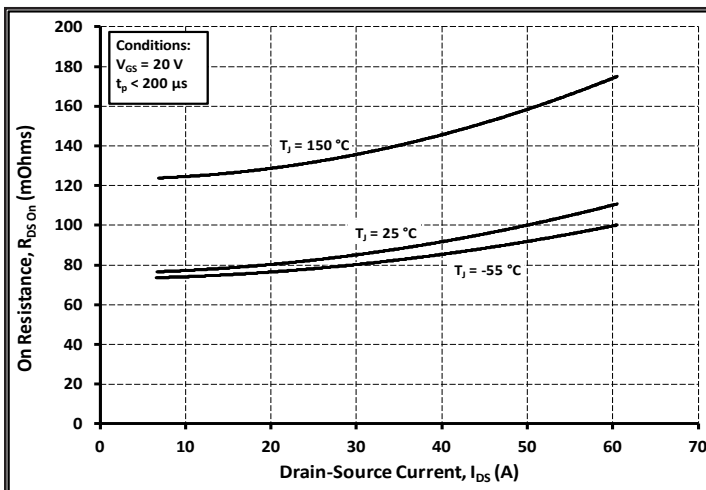
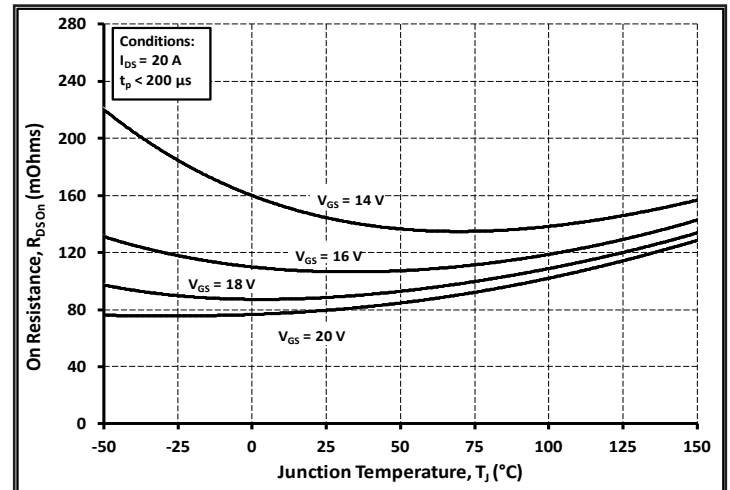

Figure 1. Output Characteristics $T_j = -55\text{ }^{\circ}\text{C}$

Figure 2. Output Characteristics $T_j = 25\text{ }^{\circ}\text{C}$

Figure 3. Output Characteristics $T_j = 150\text{ }^{\circ}\text{C}$


Figure 4. Normalized On-Resistance vs. Temperature


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

Typical Performance

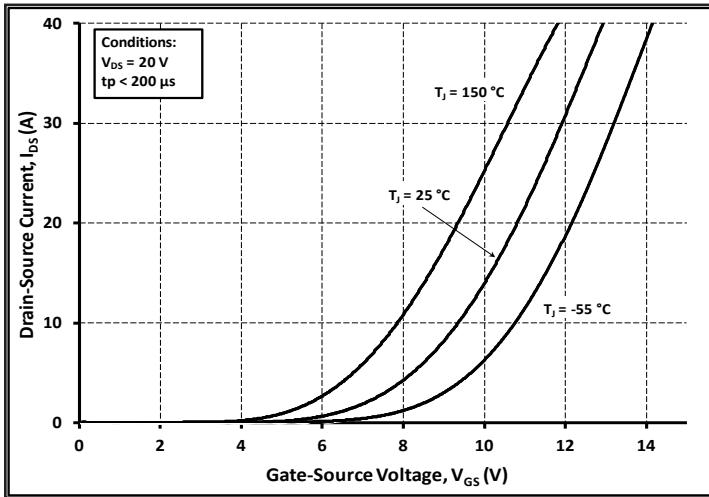


Figure 7. Transfer Characteristic for Various Junction Temperatures

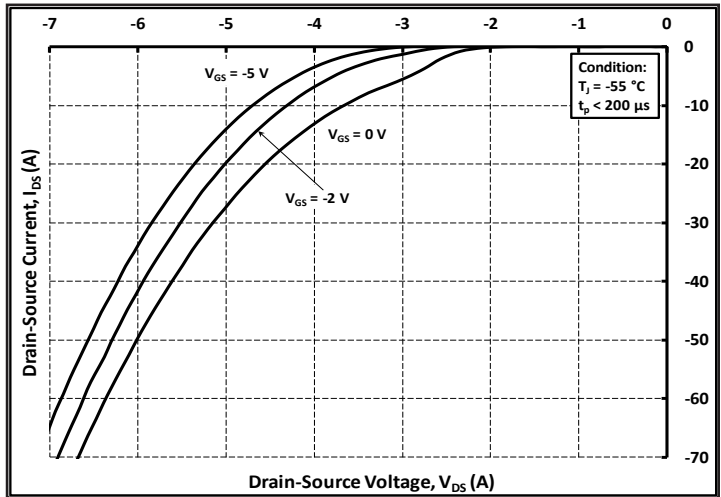


Figure 8. Body Diode Characteristic at -55 °C

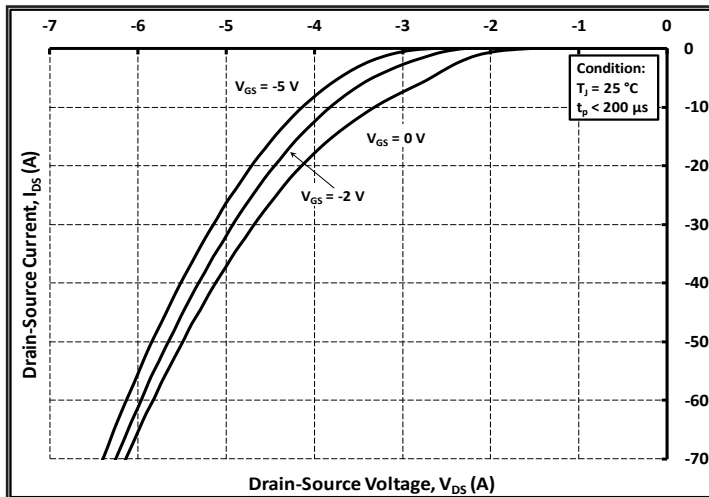


Figure 9. Body Diode Characteristic at 25 °C

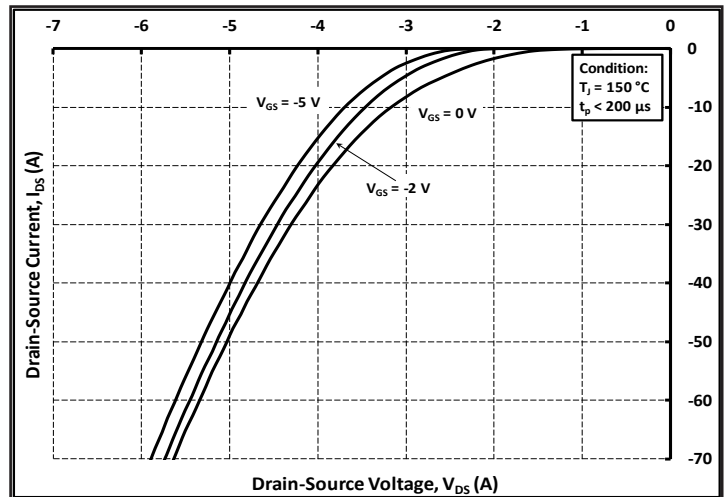


Figure 10. Body Diode Characteristic at 150 °C

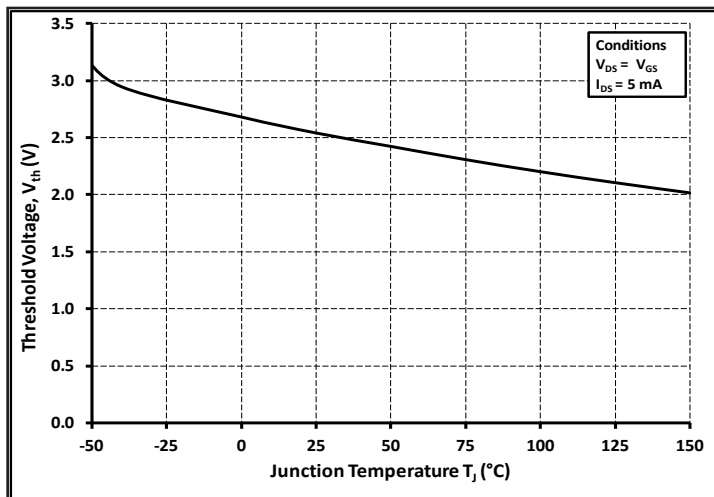


Figure 11. Threshold Voltage vs. Temperature

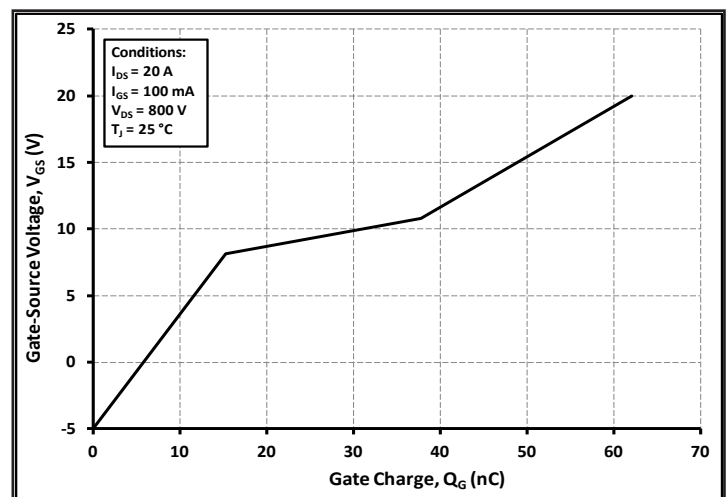


Figure 12. Gate Charge Characteristics

Typical Performance

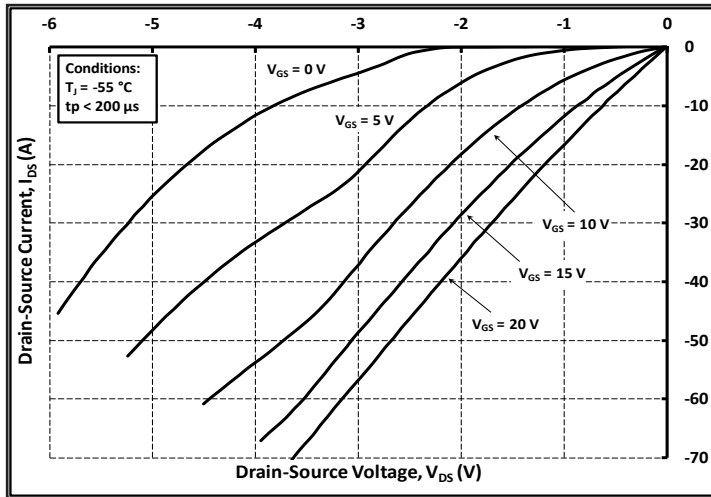


Figure 13. 3rd Quadrant Characteristic at -55 °C

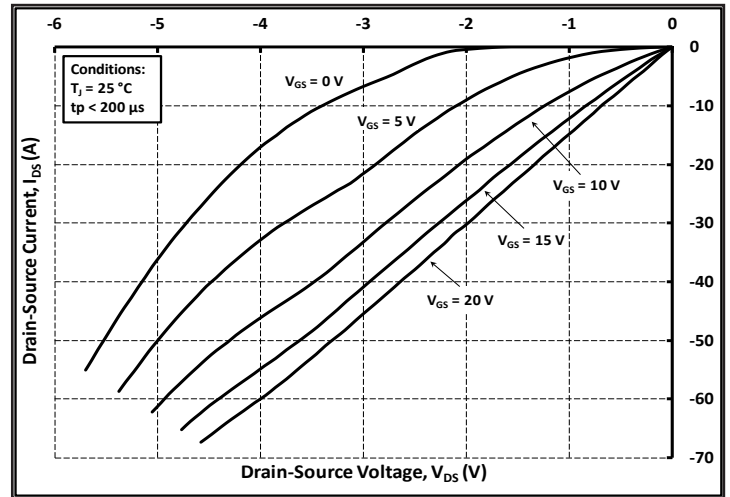


Figure 14. 3rd Quadrant Characteristic at 25 °C

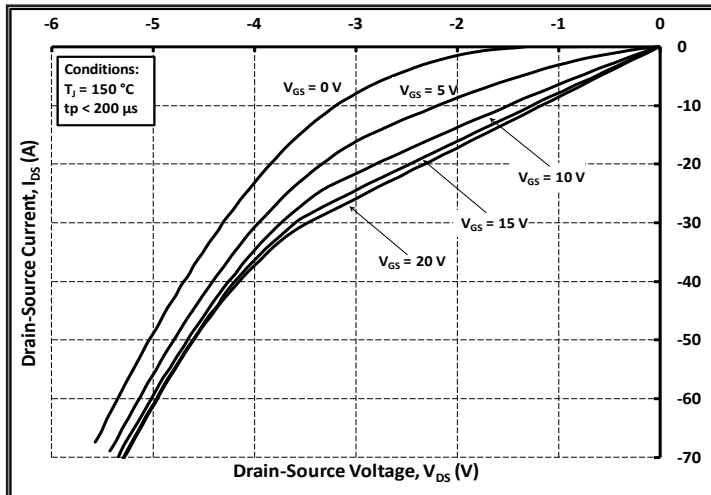


Figure 15. 3rd Quadrant Characteristic at 150 °C

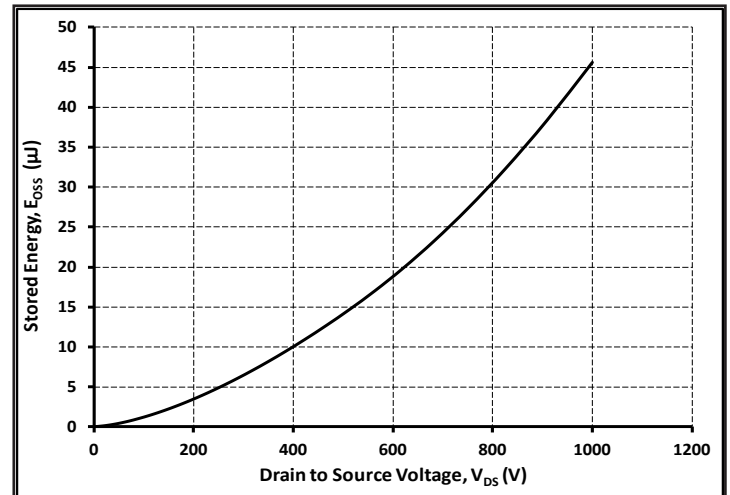


Figure 16. Output Capacitor Stored Energy

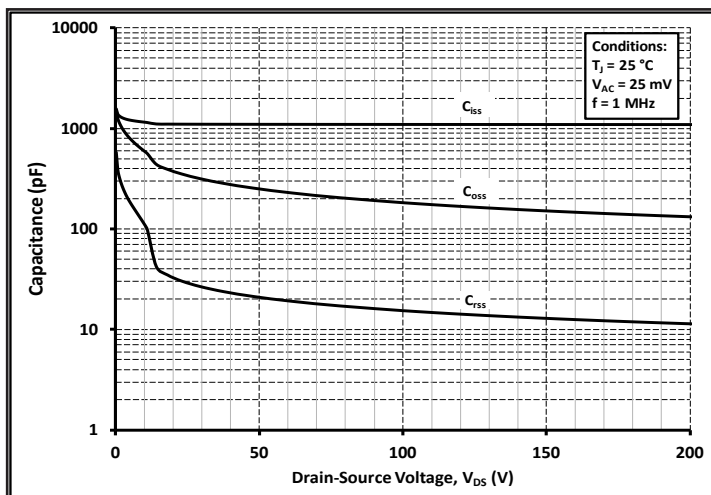


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

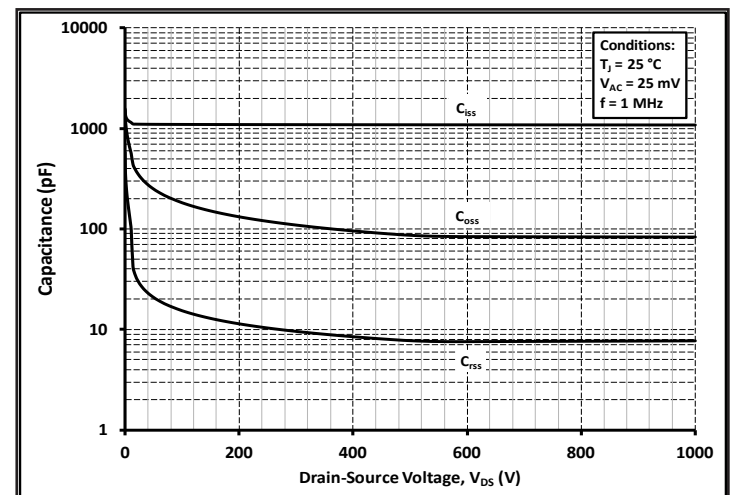


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1000V)

Typical Performance

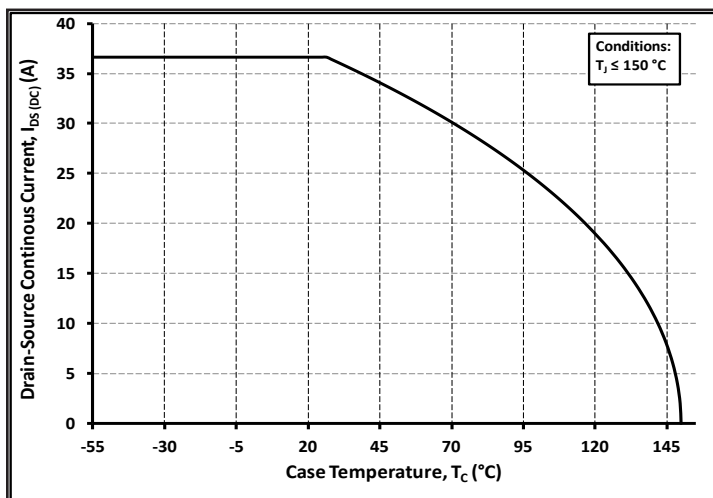


Figure 19. Continuous Drain Current Derating vs. Case Temperature

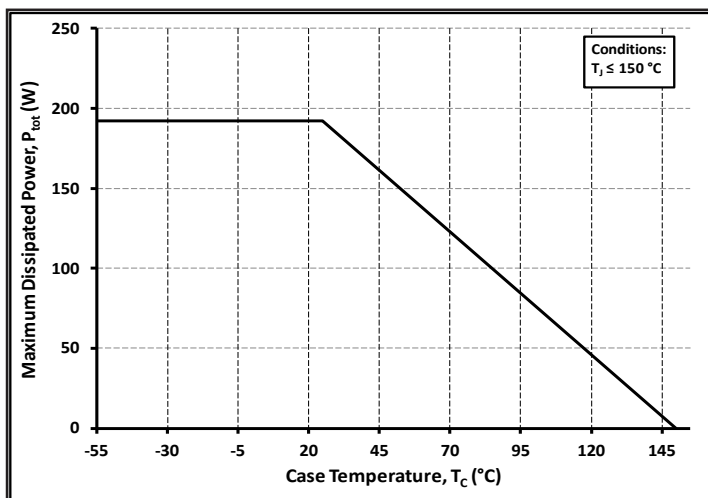


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

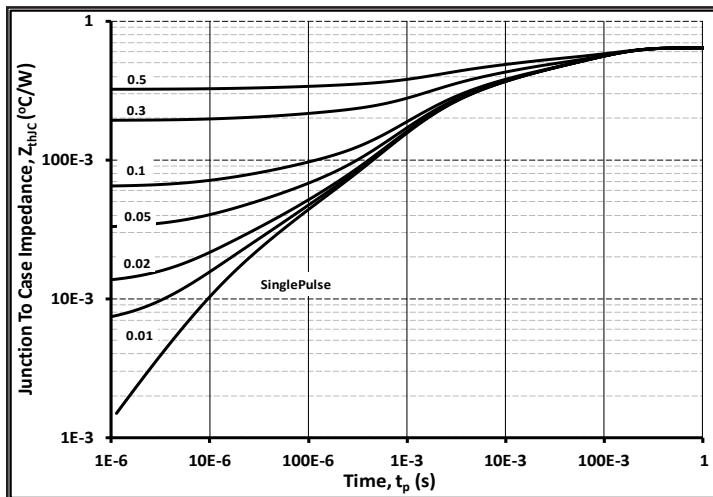


Figure 21. Transient Thermal Impedance (Junction - Case)

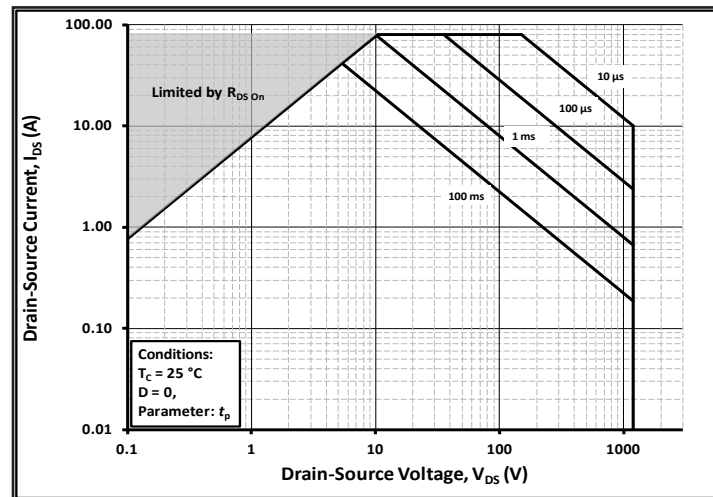


Figure 22. Safe Operating Area

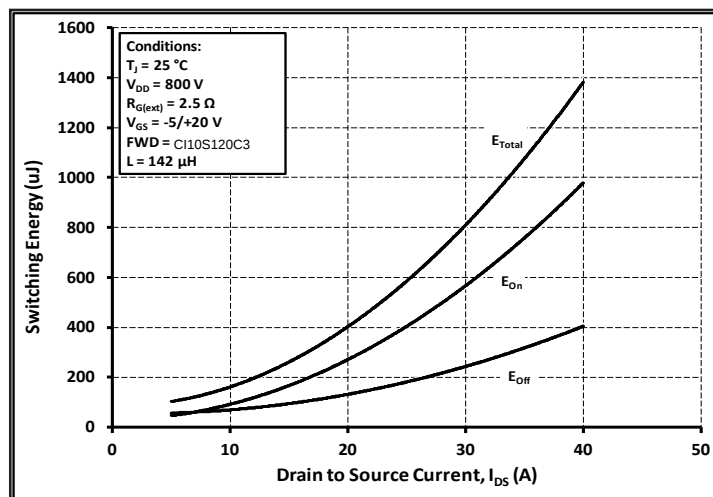


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 800V$)

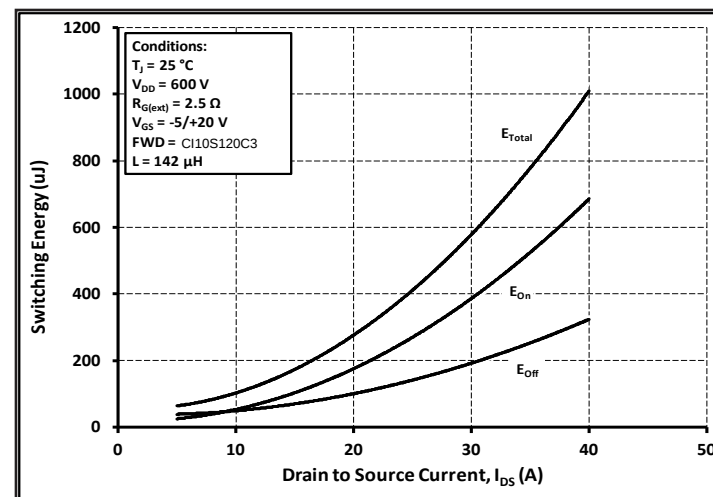


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 600V$)

Typical Performance

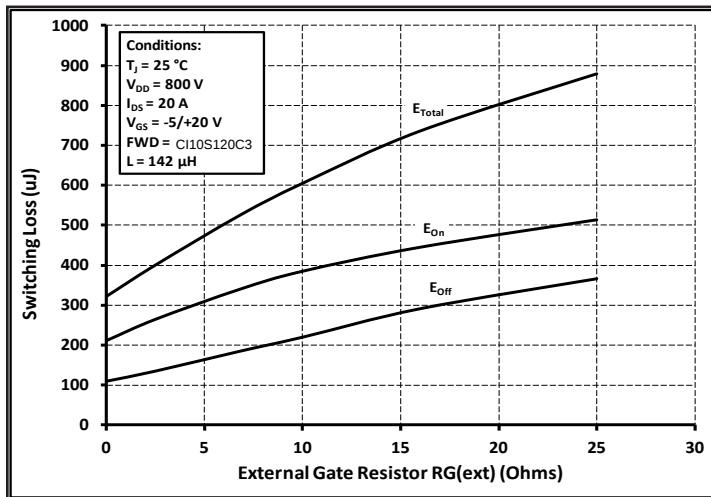


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

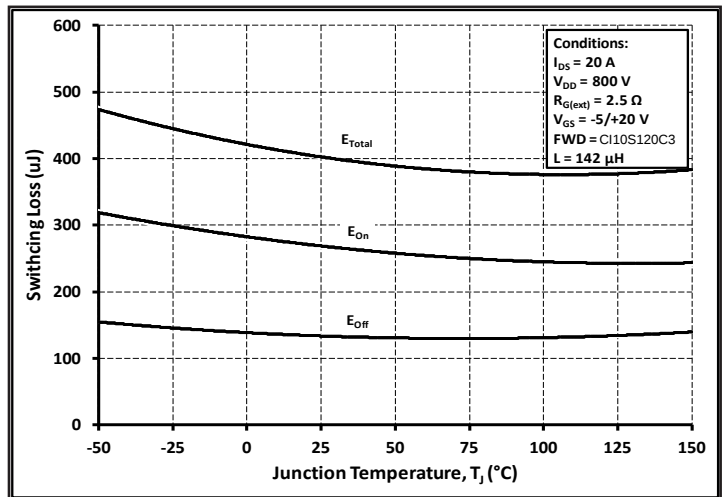


Figure 26. Clamped Inductive Switching Energy vs. Temperature

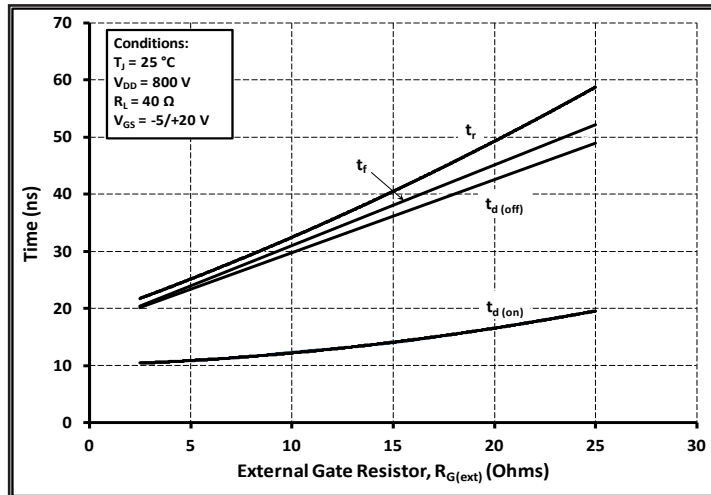


Figure 27. Switching Times vs. $R_{G(ext)}$

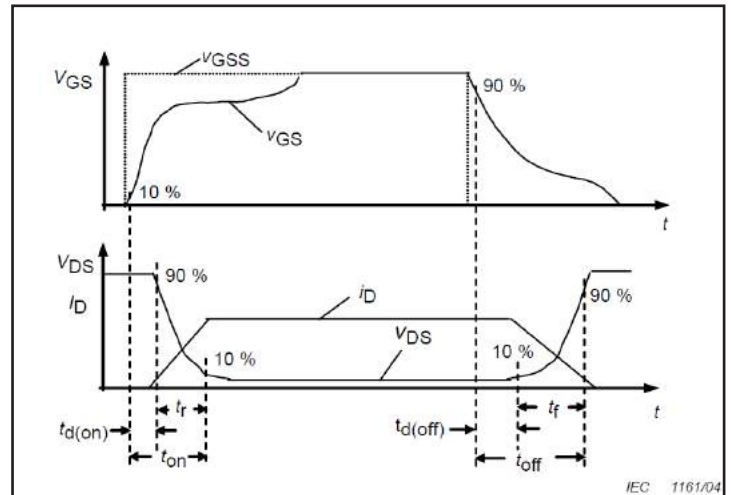


Figure 28. Switching Times Definition

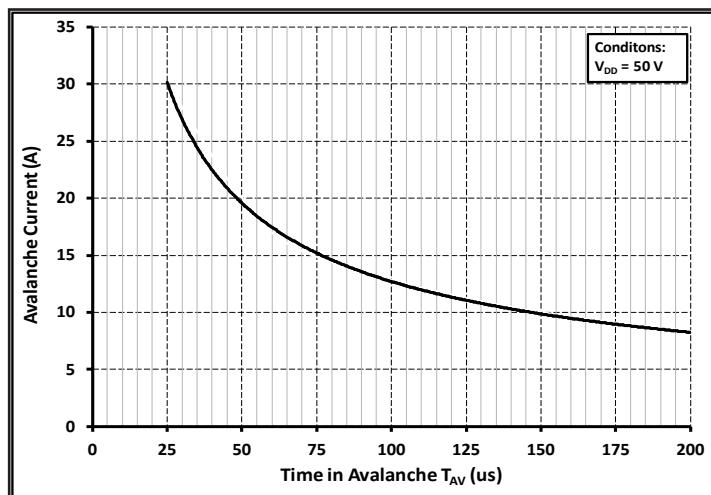


Figure 29. Single Avalanche SOA curve

Test Circuit Schematic

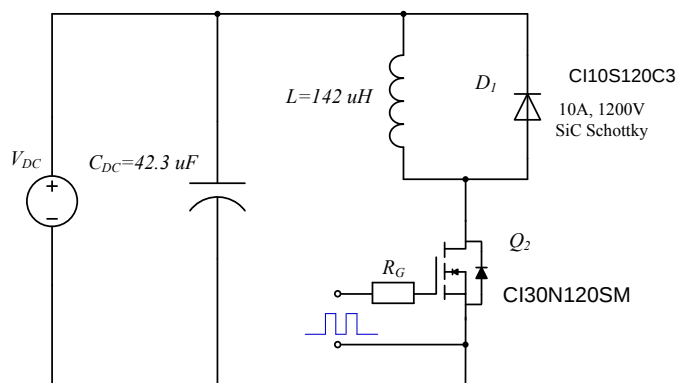


Figure 30. Clamped Inductive Switching Waveform Test Circuit

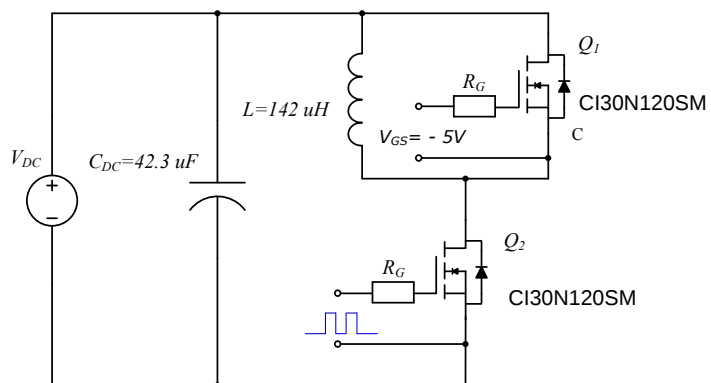
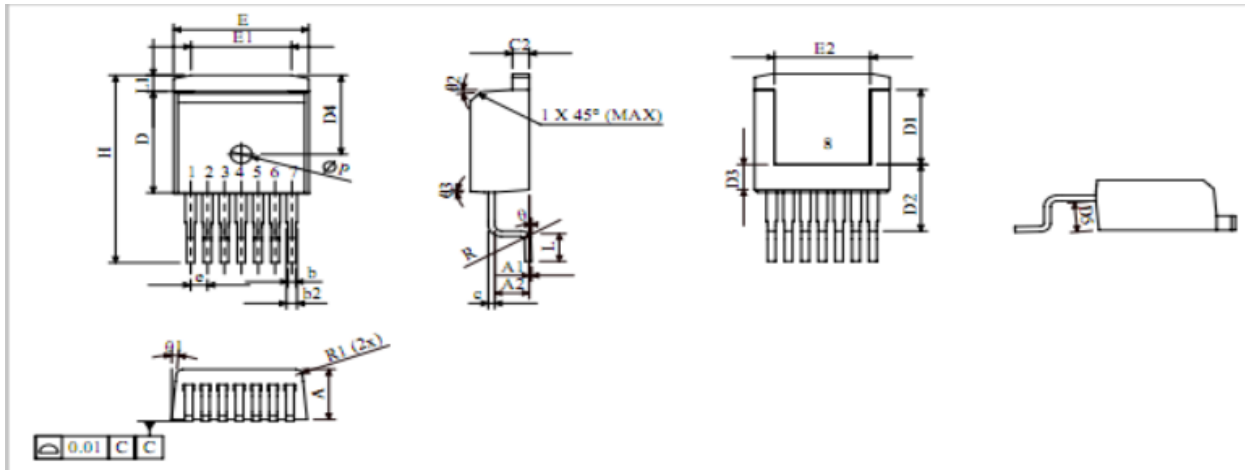


Figure 31. Body Diode Recovery Test Circuit

ESD Ratings

ESD Test	Total Devices Sampled	Resulting Classification
ESD-HBM	All Devices Passed 1000V	2 (>2000V)
ESD-MM	All Devices Passed 400V	C (>400V)
ESD-CDM	All Devices Passed 1000V	IV (>1000V)

Package Dimensions



SYMBOL	MIN (mm)	MAX (mm)
A	4.30	4.57
A1	0.00	0.25
A2	2.595 REF	
b	0.50	0.70
b2	0.60	1.00
c	0.281	0.481
C2	1.17	1.37
D	9.025	9.125
D1	6.50	6.70
D2	5.39 REF	
D3	2.148	---
D4	7.000 REF	
D5	2.555	---
A2	2.595 REF	
E	10.13	10.23
E1	6.50	8.60
E2	6.778	7.665
e	1.27 TYP	
H	15.043	17.313
L	2.324	2.700
L1	0.968	1.868
R	0.506 REF	
R1	0.500 REF	
P	1.60 REF	
θ	0°	8°
θ1	4.5°	5.5°
θ2	4°	6°
θ3	4°	6°

1	GATE
2	KELVIN
3	SOURCE
4	
5	
6	
7	DRAIN
8	